

TO-126C Plastic-Encapsulate Transistors

D882 TRANSISTOR (NPN)

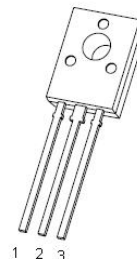
FEATURES

Power Dissipation

$P_{CM} : 1.25 \text{ W (Ta=25}^\circ\text{C)}$

TO- 126C

- 1. EMITTER
- 2. COLLECTOR
- 3. BASE



MAXIMUM RATINGS(T_A=25°C unless otherwise noted)

Symbol	Paraa Yñf	JU i Y	Unit
V _{CBO}	Collector-Base Voltage	40	V
V _{CEO}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current -Continuous	3	A
P _C	Total Device Dissipation	1.25	W
T _J	Junction Temperature	150	°C
T _{stg}	Junction and Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS(Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100µA, I _E =0	40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 10 mA, I _B =0	30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 100 mA, I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =40 V, I _E =0			1	µA
Collector cut-off current	I _{CEO}	V _{CE} =30 V, I _B =0			10	µA
Emitter cut-off current	I _{EBO}	V _{EB} =6V, I _C =0			1	µA
DC current gain	h _{FE(1)}	V _{CE} = 2V, I _C = 1A	60		400	
	h _{FE(2)}	V _{CE} =2V, I _C = 100mA	32			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =2A, I _B = 0.2A			0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =2A, I _B = 0.2A			1.5	V
Transition frequency	f _T	V _{CE} =5 V, I _C =0.1mA f = 10MHz	50			MHz

CLASSIFICATION OF h_{FE(1)}

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400